

IN THE SPECIFICATION

Replace paragraph 57 with the following:

[0057] An insulation film such as an oxide film 12 is formed on the portion of the n-type drift region 1 between the gate electrode 8 and the n⁺-type drain region 9 such that the oxide film 12 is thinner on the side of the gate electrode 8 and thicker on the side of the n⁺-type drain region 9. A field plate 13 is formed on the oxide film 12. A drain electrode 10 is formed on the n⁺-type drain region 9. A source electrode 6 is formed on the n⁺-type source region 5 and the p⁺-type contact region 4. The source electrode 6 and the field plate 13 are connected electrically to each other. An interlayer insulation film ~~(not shown)~~ IIF is formed between the gate electrode 8 and the source electrode 6 to insulate the gate electrode 8 and the source electrode 6 from each other. The oxide film 12 is thinner than the interlayer insulation film.